



**Si4925BDY**  
Vishay Siliconix

**Dual P-Channel 30-V (D-S) MOSFET**

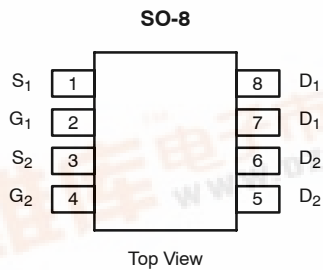
PRODUCT SUMMARY		
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
-30	0.025 @ V <sub>GS</sub> = -10 V	-7.1
	0.041 @ V <sub>GS</sub> = -4.5 V	-5.5

**FEATURES**

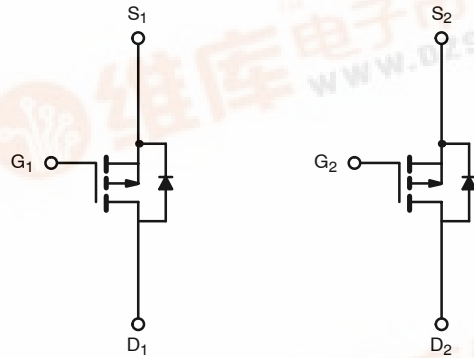
- TrenchFET® Power MOSFET
- Advanced High Cell Density Process

**APPLICATIONS**

- Load Switches
  - Notebook PCs
  - Desktop PCs
  - Game Stations



Ordering Information: Si4925BDY  
Si4925BDY-T1 (with Tape and Reel)



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-30		V	
Gate-Source Voltage	V <sub>GS</sub>	±20			
Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25°C	-7.1	-5.3	A
		T <sub>A</sub> = 70°C	-5.7	-4.3	
Pulsed Drain Current	I <sub>DM</sub>	-40		A	
continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	-1.7	-0.9		
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25°C	2.0	1.1	W
		T <sub>A</sub> = 70°C	1.3	0.7	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	t ≤ 10 sec	50	62.5	°C/W
		Steady State	85	110	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	30	40		

Notes:  
a. Surface Mounted on 1" x 1" FR4 Board.

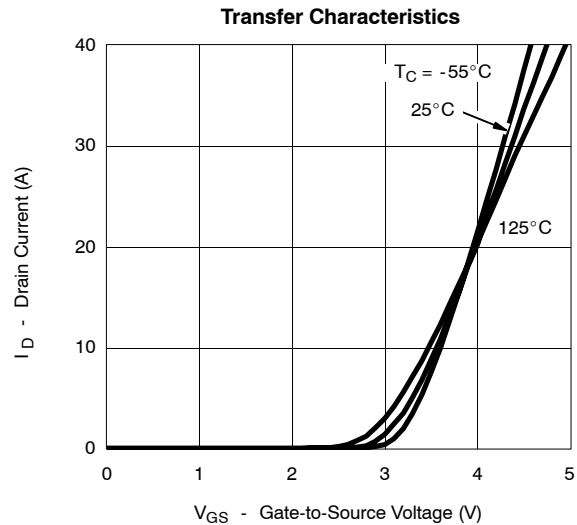
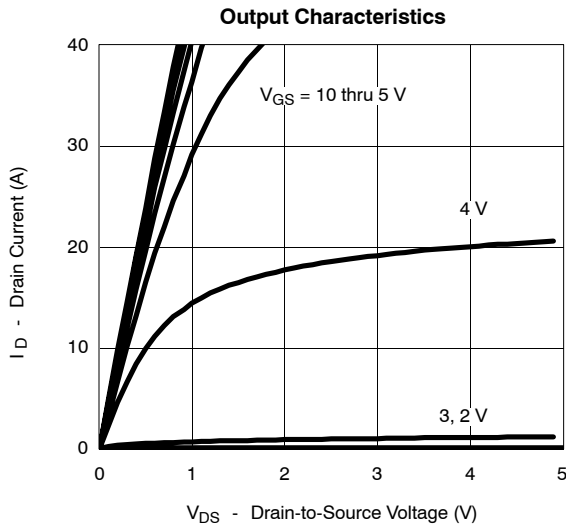


<b>SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)</b>						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1		-3	V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V			-1	μA
		V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			-25	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -10 V	-40			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -7.1 A		0.020	0.025	Ω
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -5.5 A		0.033	0.041	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -7.1 A		20		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = -1.7 A, V <sub>GS</sub> = 0 V		-0.8	-1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -7.1 A		33	50	nC
Gate-Source Charge	Q <sub>gs</sub>			5.4		
Gate-Drain Charge	Q <sub>gd</sub>			8.9		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15 V, R <sub>L</sub> = 15 Ω I <sub>D</sub> ≅ -1 A, V <sub>GEN</sub> = -10 V, R <sub>G</sub> = 6 Ω		9	15	ns
Rise Time	t <sub>r</sub>			12	20	
Turn-Off Delay Time	t <sub>d(off)</sub>			60	90	
Fall Time	t <sub>f</sub>			34	50	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>		I <sub>F</sub> = -1.7 A, di/dt = 100 A/μs		30	

**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

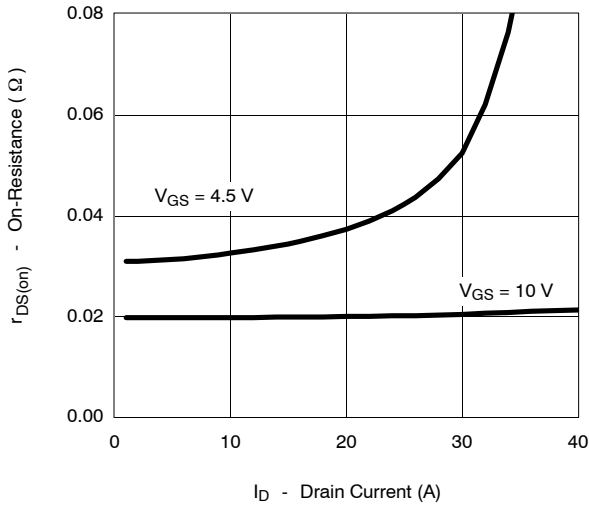
**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



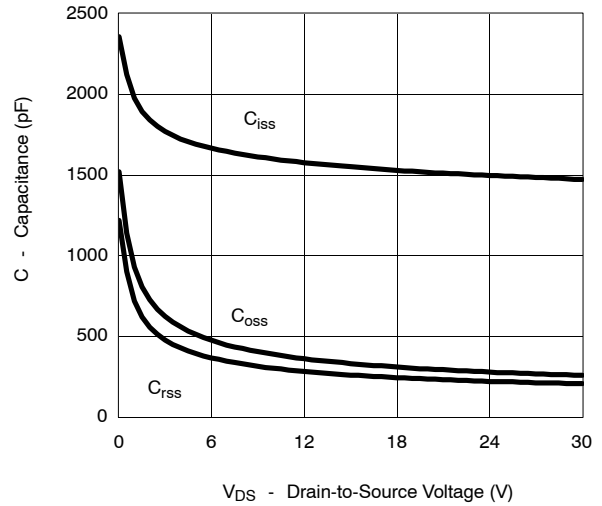


**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

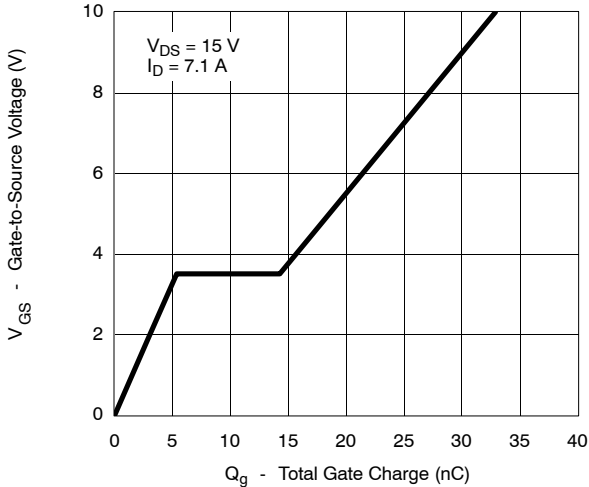
**On-Resistance vs. Drain Current**



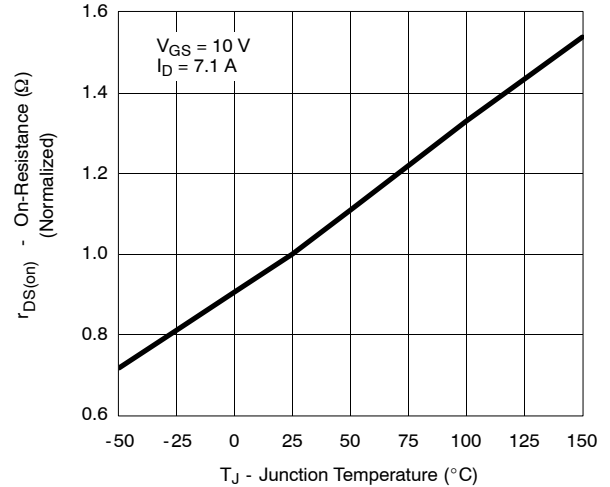
**Capacitance**



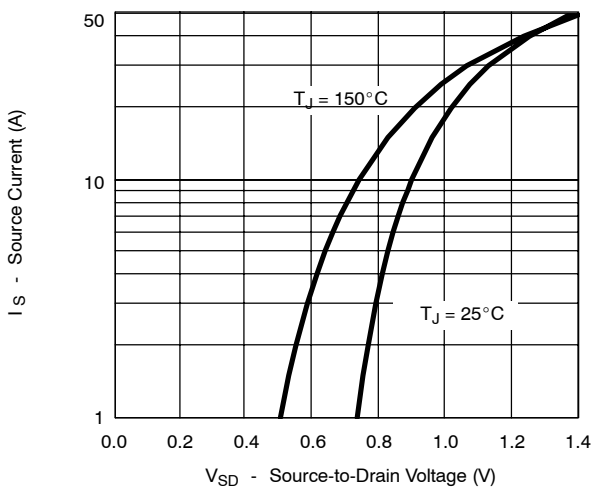
**Gate Charge**



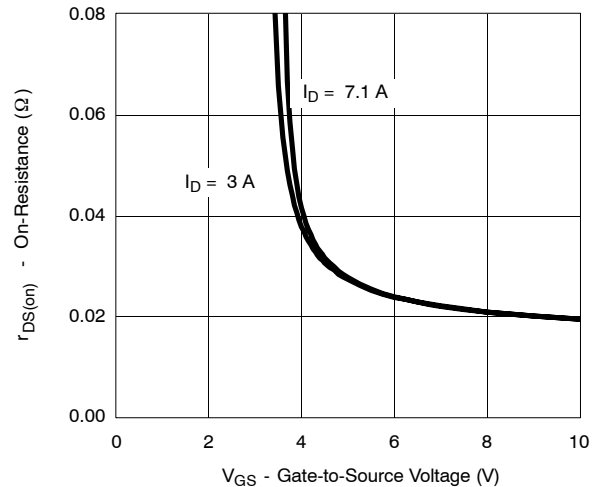
**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**

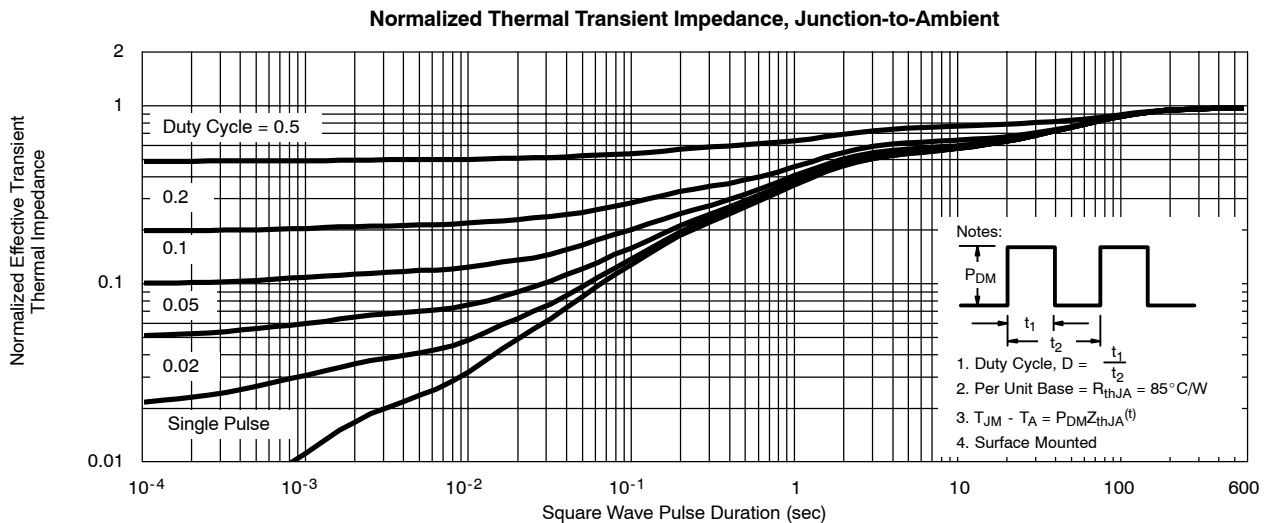
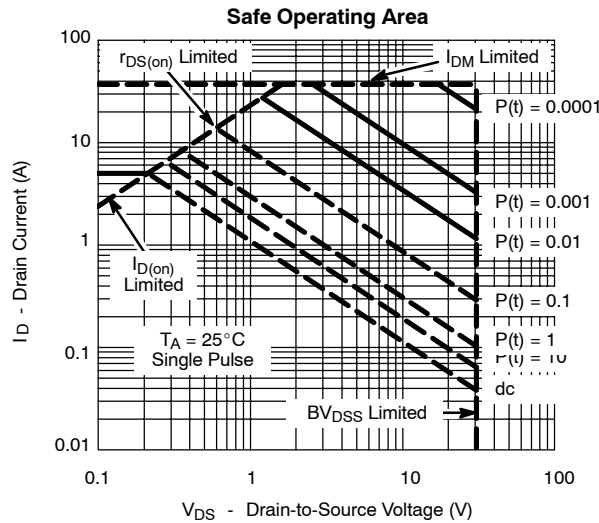
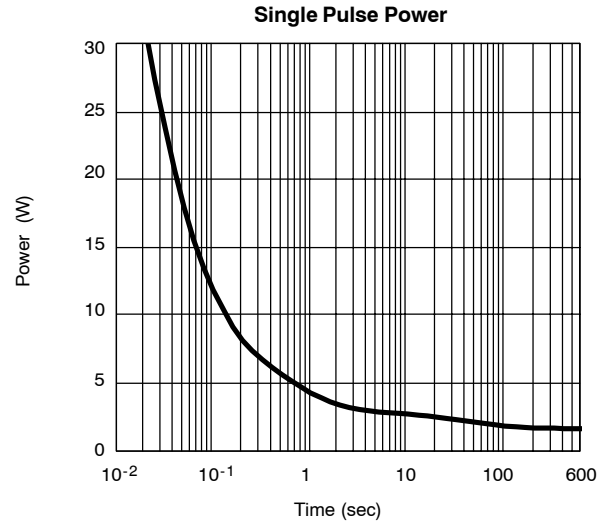
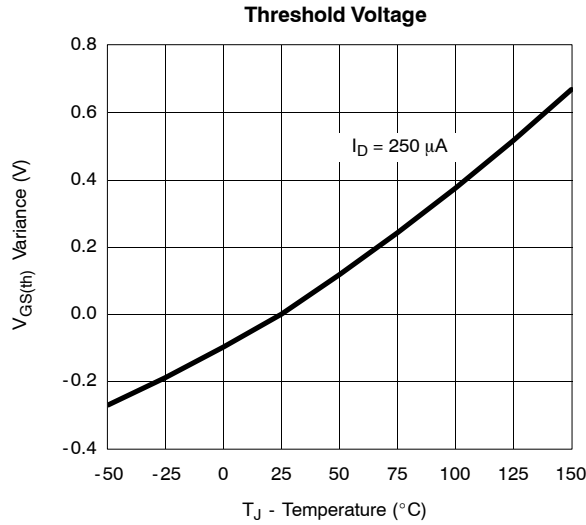


**On-Resistance vs. Gate-to-Source Voltage**





**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**





**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

